

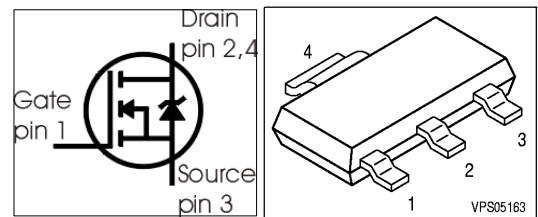
**SIPMOS<sup>®</sup> Power-Transistor**
**Feature**

- N-Channel
- Enhancement mode
- Logic Level
- dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101
- Halogen-free according to IEC61249-2-21


**Product Summary**

$V_{DS}$	600	V
$R_{DS(on)}$	45	$\Omega$
$I_D$	0.12	A

PG-SOT223



Type	Package	RoHS compliant	Tape and Reel Information	Marking	Packaging
BSP125	PG-SOT223	Yes	H6433: 4000 pcs/reel	BSP125	Non dry
BSP125	PG-SOT223	Yes	H6327: 1000 pcs/reel	BSP125	Non dry

**Maximum Ratings, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Value	Unit
Continuous drain current $T_A=25^\circ\text{C}$ $T_A=70^\circ\text{C}$	$I_D$	0.12 0.1	A
Pulsed drain current $T_A=25^\circ\text{C}$	$I_{D\text{ puls}}$	0.48	
Reverse diode dv/dt $I_S=0.12\text{A}$ , $V_{DS}=480\text{V}$ , $di/dt=200\text{A}/\mu\text{s}$ , $T_{j\text{max}}=175^\circ\text{C}$	dv/dt	6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$	$\pm 20$	V
ESD Class (JESD22-A114-HBM)		1A (>250V, <500V)	
Power dissipation $T_A=25^\circ\text{C}$ , $T_A=25$	$P_{\text{tot}}$	1.8	W
Operating and storage temperature IEC climatic category; DIN IEC 68-1	$T_j$ , $T_{\text{stg}}$	-55... +150 55/150/56	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - soldering point (Pin 4)	$R_{thJS}$	-	-	25	K/W
SMD version, device on PCB:	$R_{thJA}$	-	-	115	
@ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>1)</sup>		-	-	70	

**Electrical Characteristics, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain-source breakdown voltage $V_{GS}=0, I_D=0.25\text{mA}$	$V_{(BR)DSS}$	600	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=94\mu\text{A}$	$V_{GS(th)}$	1.3	1.9	2.3	
Zero gate voltage drain current $V_{DS}=600\text{V}, V_{GS}=0, T_j=25^\circ\text{C}$ $V_{DS}=600\text{V}, V_{GS}=0, T_j=125^\circ\text{C}$	$I_{DSS}$	-	-	0.1 5	$\mu\text{A}$
Gate-source leakage current $V_{GS}=20\text{V}, V_{DS}=0$	$I_{GSS}$	-	10	100	
Drain-source on-state resistance $V_{GS}=4.5\text{V}, I_D=0.11\text{A}$	$R_{DS(on)}$	-	26	60	$\Omega$
Drain-source on-state resistance $V_{GS}=10\text{V}, I_D=0.12\text{A}$	$R_{DS(on)}$	-	25	45	

<sup>1)</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic Characteristics**

Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 0.1\text{A}$	0.06	0.18	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0, V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$	-	100	150	pF
Output capacitance	$C_{oss}$		-	8.2	12.3	
Reverse transfer capacitance	$C_{rss}$		-	3.2	4.8	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 300\text{V}, V_{GS} = 10\text{V}$ , $I_D = 0.13\text{A}, R_G = 6\Omega$	-	7.7	11.6	ns
Rise time	$t_r$		-	14.4	21	
Turn-off delay time	$t_{d(off)}$		-	20	30	
Fall time	$t_f$		-	110	165	

**Gate Charge Characteristics**

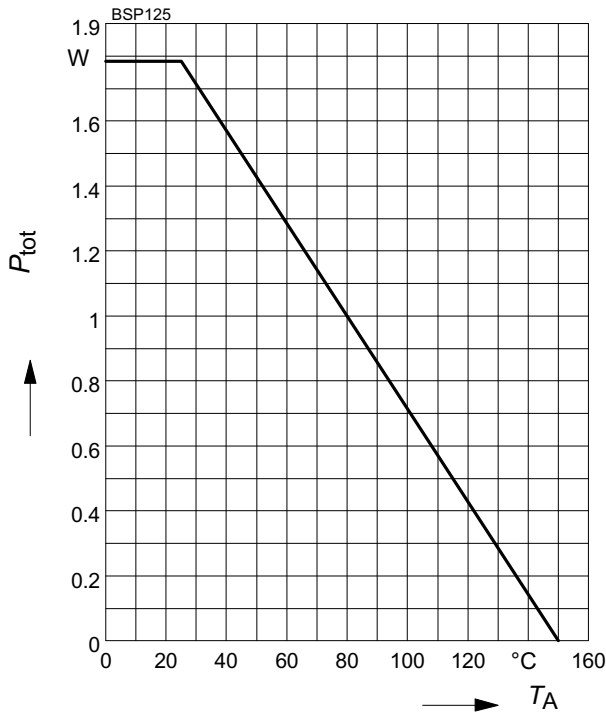
Gate to source charge	$Q_{gs}$	$V_{DD} = 400\text{V}, I_D = 0.13\text{A}$	-	0.27	0.3	nC
Gate to drain charge	$Q_{gd}$		-	2.3	3.5	
Gate charge total	$Q_g$	$V_{DD} = 400\text{V}, I_D = 0.13\text{A}$ , $V_{GS} = 0 \text{ to } 10\text{V}$	-	4.4	6.6	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 400\text{V}, I_D = 0.13\text{A}$	-	3.44	-	V

**Reverse Diode**

Inverse diode continuous forward current	$I_S$	$T_A = 25\text{ }^\circ\text{C}$	-	-	0.12	A
Inv. diode direct current, pulsed	$I_{SM}$		-	-	0.48	
Inverse diode forward voltage	$V_{SD}$	$V_{GS} = 0, I_F = 0.12\text{A}$	-	0.8	1.2	V
Reverse recovery time	$t_{rr}$	$V_R = 300\text{V}, I_F = I_S$ , $di_F/dt = 100\text{A}/\mu\text{s}$	-	156	235	ns
Reverse recovery charge	$Q_{rr}$		-	165	250	

### 1 Power dissipation

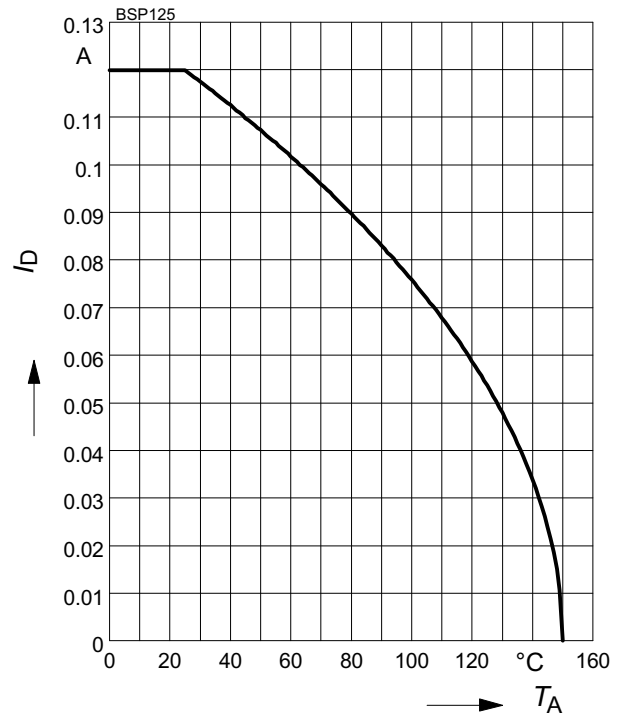
$$P_{tot} = f(T_A)$$



### 2 Drain current

$$I_D = f(T_A)$$

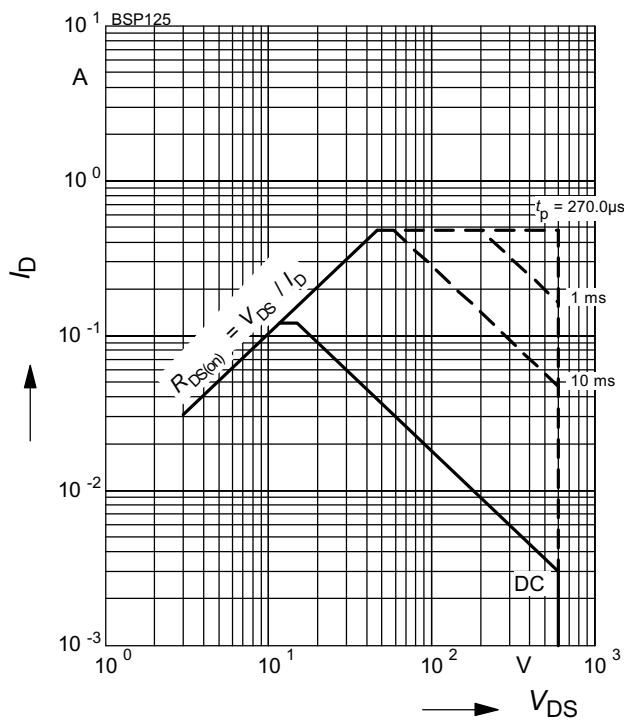
parameter:  $V_{GS} \geq 10\text{ V}$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

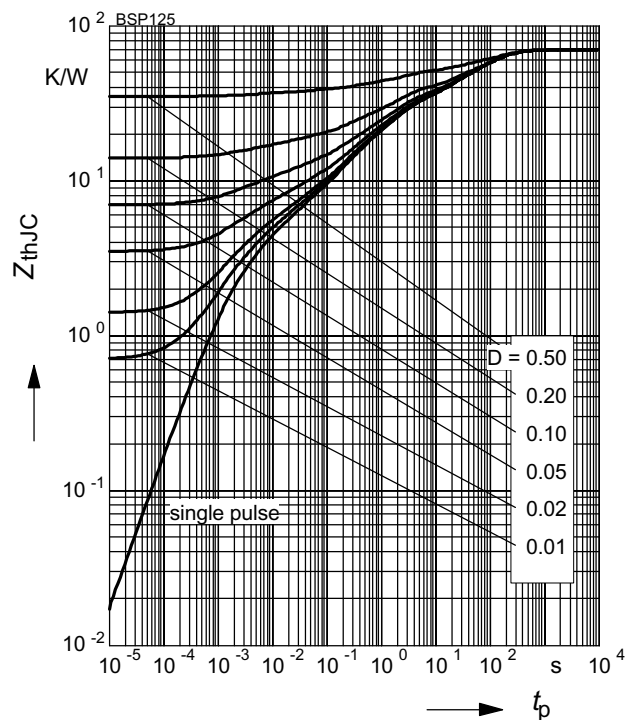
parameter:  $D = 0, T_A = 25$



### 4 Transient thermal impedance

$$Z_{thJA} = f(t_p)$$

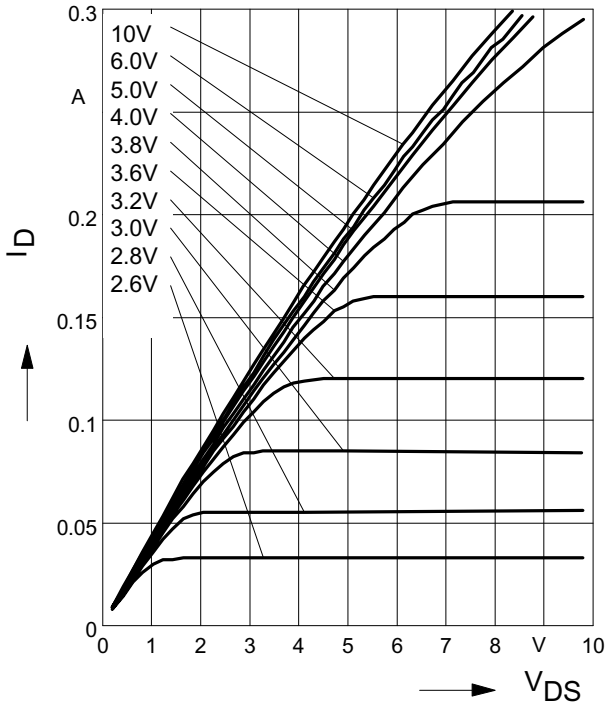
parameter:  $D = t_p/T$



**5 Typ. output characteristic**

$I_D = f(V_{DS})$

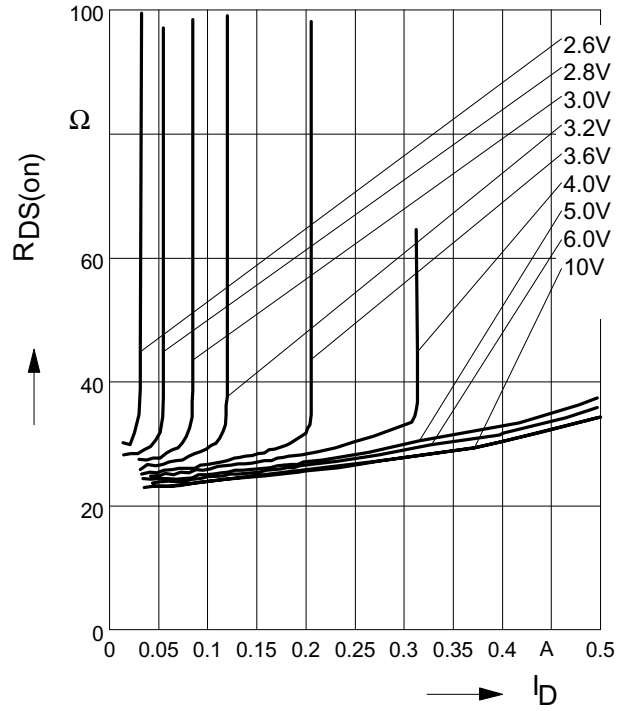
parameter:  $T_j = 25\text{ }^\circ\text{C}$ ,  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

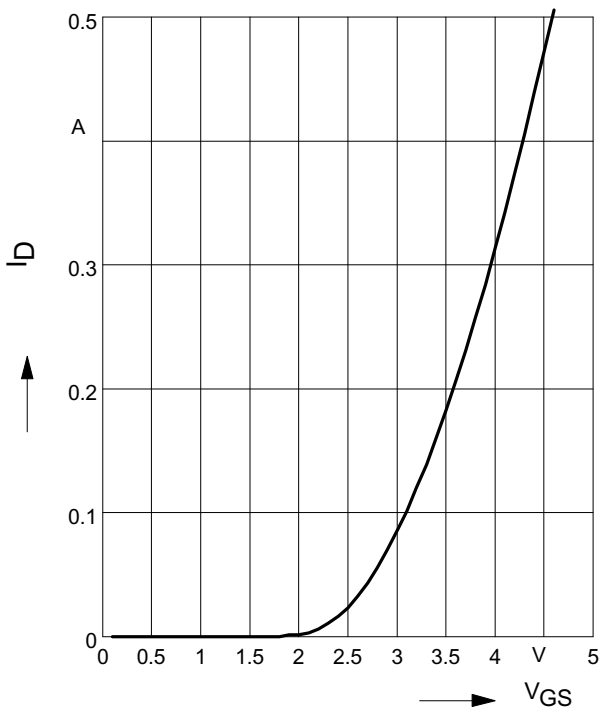
parameter:  $T_j = 25\text{ }^\circ\text{C}$ ,  $V_{GS}$



**7 Typ. transfer characteristics**

$I_D = f(V_{GS})$ ;  $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

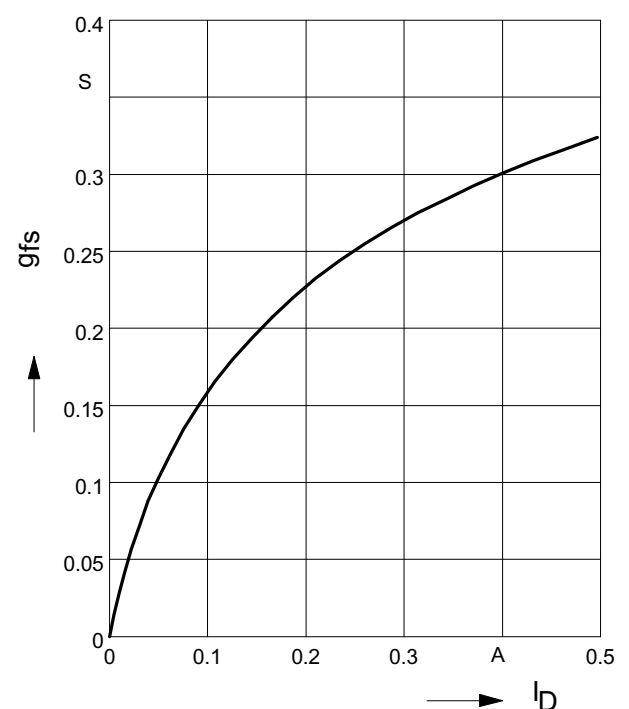
parameter:  $T_j = 25\text{ }^\circ\text{C}$



**8 Typ. forward transconductance**

$g_{fs} = f(I_D)$

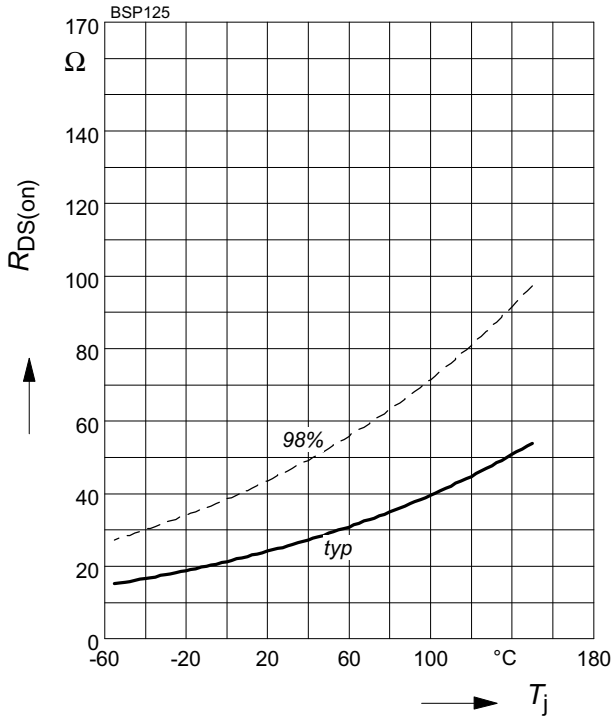
parameter:  $T_j = 25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

$$R_{DS(on)} = f(T_j)$$

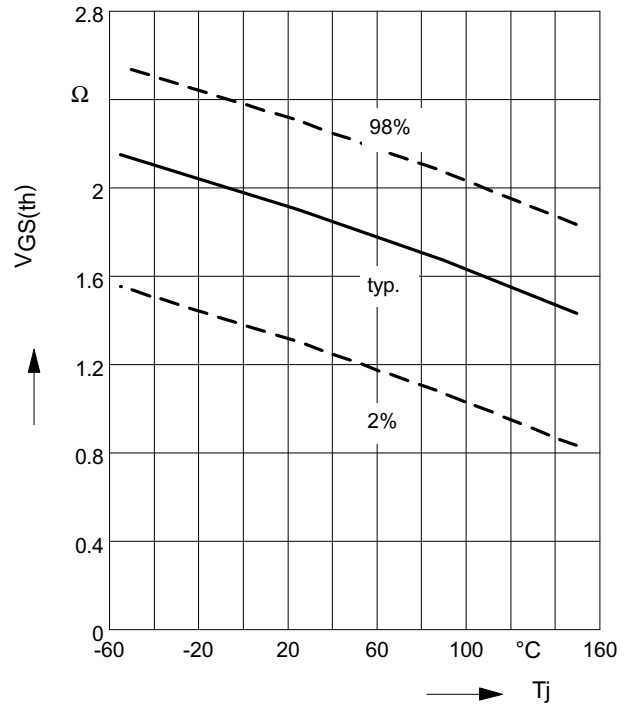
parameter :  $I_D = 0.12 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$



**(.) Typ. gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

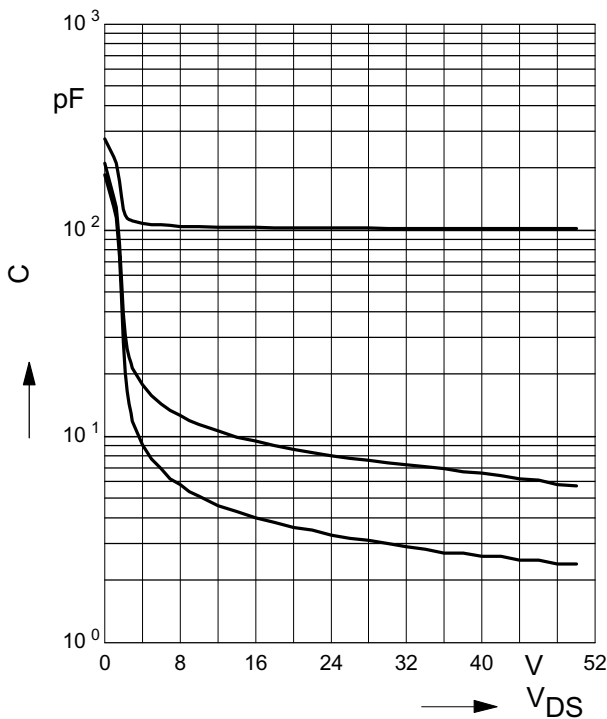
parameter:  $V_{GS} = V_{DS}$ ;  $I_D = 94 \mu\text{A}$



**11 Typ. capacitances**

$$C = f(V_{DS})$$

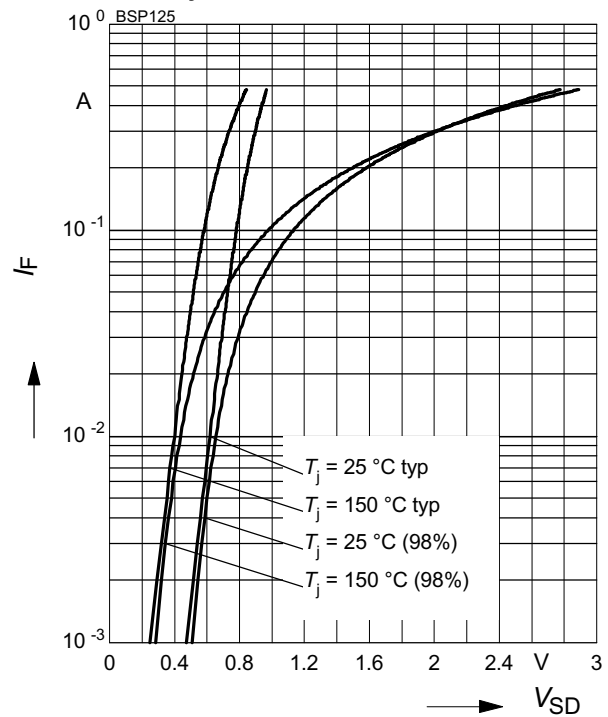
parameter:  $V_{GS}=0$ ,  $f=1 \text{ MHz}$ ,  $T_j = 25 \text{ }^\circ\text{C}$



**12 Forward character. of reverse diode**

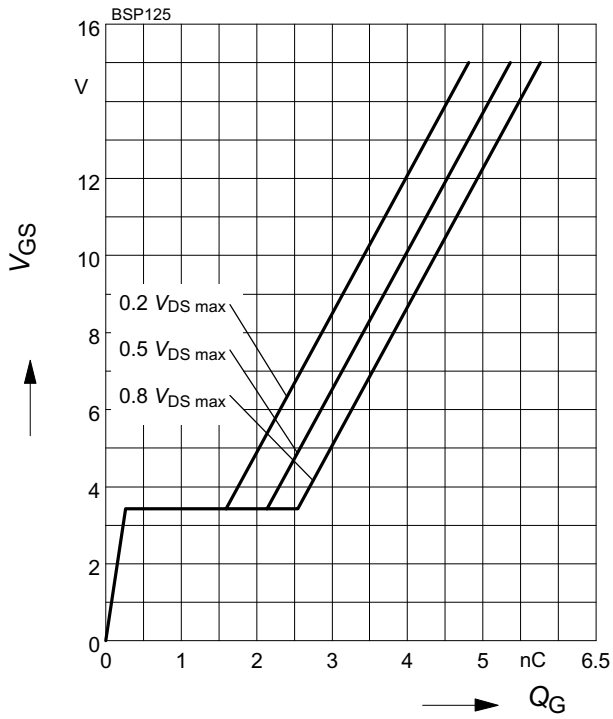
$$I_F = f(V_{SD})$$

parameter:  $T_j$



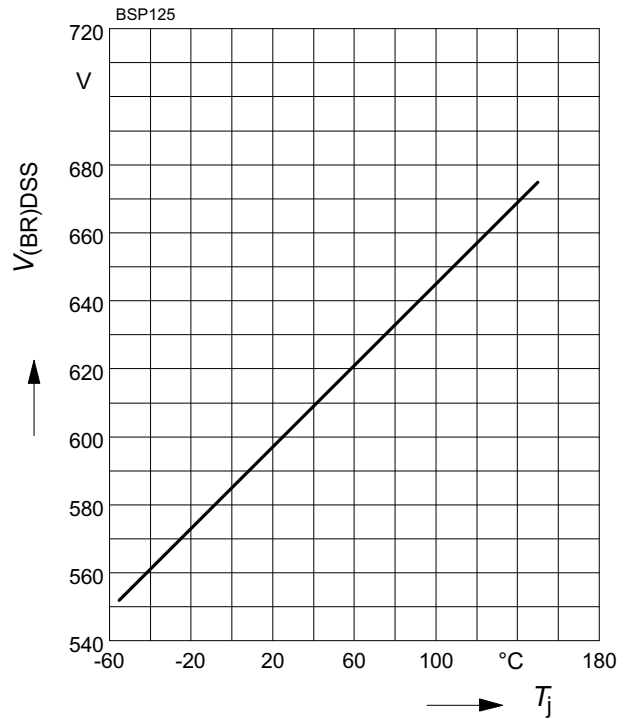
**13 Typ. gate charge**

$V_{GS} = f(Q_G)$ ; parameter:  $V_{DS}$ ,  
 $I_D = 0.12$  A pulsed,  $T_j = 25$  °C



**14 Drain-source breakdown voltage**

$V_{(BR)DSS} = f(T_j)$



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